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## PATENT ABSTRACTS OF JAPAN

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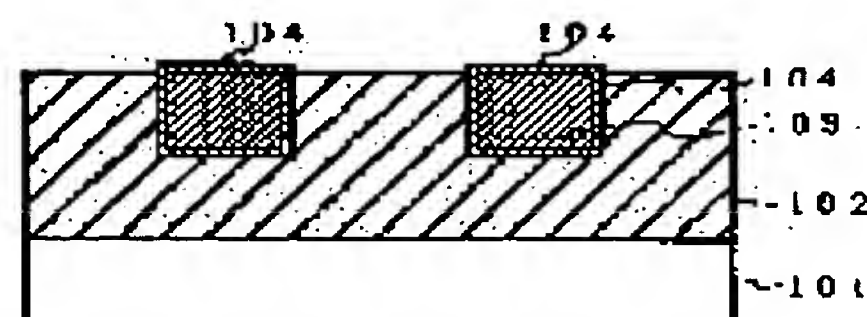
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## (54) WIRING STRUCTURE OF SEMICONDUCTOR DEVICE AND MANUFACTURE THEREOF

## (57)Abstract:

PROBLEM TO BE SOLVED: To easily form a Cu diffusion blocking film in connecting trenches having a more fine diameter and high aspect ratio in a multilayer wiring structure using Cu as a wiring material and using a material having a high adhesion to Cu and low contact resistance as a base film.

SOLUTION: On a substrate 101 having elements e.g. transistors a Cu or Cu alloy wiring 103 is formed through a layer insulation film 102 and covered with a barrier film 104 made of Ru, Os, Ir or Rh.



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